# NTMFS4122N

# Power MOSFET

## 30 V, 23 A, Single N−Channel, SO−8 Flat Lead

### Features

- Low $R_{DS(on)}$
- Low Inductance SO−8 Package
- These are Pb−Free Devices

### Applications

- Notebooks, Graphics Cards
- DC−DC Converters
- Synchronous Rectification

**MAXIMUM RATINGS** ($T_J$ = 25°C unless otherwise noted)

| Parameter | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain−to−Source Voltage | | | $V_{DSS}$ | 30 | V |
| Gate−to−Source Voltage | | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current (Note 1 ) | Steady State | $T_A$ = 25°C | $I_D$ | 14 | A |
| | | $T_A$ = 85°C | | 10 | |
| | t ≤ 10 s | $T_A$ = 25°C | | 23 | |
| Power Dissipation (Note 1) | Steady State | $T_A$ = 25°C | $P_D$ | 2.2 | W |
| | t ≤ 10 s | | | 5.8 | |
| Continuous Drain Current (Note 2) | Steady State | $T_A$ = 25°C | $I_D$ | 9.1 | A |
| | | $T_A$ = 85°C | | 6.5 | |
| Power Dissipation (Note 2) | | $T_A$ = 25°C | $P_D$ | 0.9 | W |
| Pulsed Drain Current | $t_p$ = 10 μs | | $I_{DM}$ | 68 | A |
| Operating Junction and Storage Temperature | | | $T_J$, $T_{stg}$ | −55 to 150 | °C |
| Source Current (Body Diode) | | | $I_S$ | 7.0 | A |
| Single Pulse Drain−to−Source Avalanche Energy ($V_{DD}$ = 30 V, $V_{GS}$ = 10 V, $I_{PK}$ = 21 A, L = 1 mH, $R_G$ = 25 Ω) | | | $E_{AS}$ | 220 | mJ |
| Lead Temperature for Soldering Purposes (1/8″ from case for 10 s) | | | $T_L$ | 260 | °C |

**THERMAL RESISTANCE MAXIMUM RATINGS**

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Junction−to−Ambient − Steady State (Note 1) | $R_{\theta JA}$ | 56.3 | °C/W |
| Junction−to−Ambient − t ≤ 10 s (Note 1) | $R_{\theta JA}$ | 21.5 | |
| Junction−to−Ambient − Steady State (Note 2) | $R_{\theta JA}$ | 141.6 | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface mounted on FR4 board using the minimum recommended pad size (Cu area = 0.0264 in sq).

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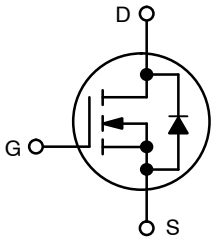
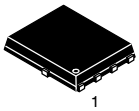
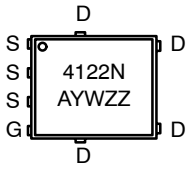
| $V_{(BR)DSS}$ | $R_{DS(on)}$ TYP | $I_D$ MAX (Note 1) |
|---|---|---|
| 30 V | 4.6 mΩ @ 10 V | 23 A |
| | 6.3 mΩ @ 4.5 V | |




**SO−8 FLAT LEAD CASE 488AA STYLE 1**

**MARKING DIAGRAM**




4122N = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

**ORDERING INFORMATION**

| Device | Package | Shipping† |
|---|---|---|
| NTMFS4122NT1G | SO−8 FL (Pb−Free) | 1500 Tape & Reel |
| NTMFS4122NT3G | SO−8 FL (Pb−Free) | 5000 Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise noted)

| Characteristic | Symbol | Test Condition | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain−to−Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | | 30 | | | V |
| Drain−to−Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | | 23 | | mV/°C |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 24 V | $T_J$ = 25°C | | | 1.0 | μA |
| | | | $T_J$ = 125°C | | | 10 | |
| Gate−to−Source Leakage Current | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = 20 V | | | | 100 | nA |
| **ON CHARACTERISTICS** (Note 3) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS}$ = $V_{DS}$, $I_D$ = 250 μA | | 1.0 | | 2.5 | V |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | | 6.6 | | mV/°C |
| Drain−to−Source On Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 14 A | | | 4.6 | 6.0 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 12 A | | | 6.3 | 8.5 | |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = 15 V, $I_D$ = 10 A | | | 13.2 | | S |
| **CHARGES, CAPACITANCES AND GATE RESISTANCE** | | | | | | | |
| Input Capacitance | $C_{ISS}$ | $V_{GS}$ = 0 V, f = 1.0 MHz, $V_{DS}$ = 24 V | | | 2310 | | pF |
| Output Capacitance | $C_{OSS}$ | | | | 460 | | |
| Reverse Transfer Capacitance | $C_{RSS}$ | | | | 263 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 15 V, $I_D$ = 12 A | | | 20 | 30 | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | | 3.0 | | |
| Gate−to−Source Charge | $Q_{GS}$ | | | | 6.7 | | |
| Gate−to−Drain Charge | $Q_{GD}$ | | | | 8.1 | | |
| Gate Resistance | $R_G$ | | | | 0.7 | | Ω |
| **SWITCHING CHARACTERISTICS** (Note 4) | | | | | | | |
| Turn−On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 15 V, $I_D$ = 1.0 A, $R_L$ = 15 Ω, $R_G$ = 3.0 Ω | | | 20 | | ns |
| Rise Time | $t_r$ | | | | 20 | | |
| Turn−Off Delay Time | $t_{d(OFF)}$ | | | | 30 | | |
| Fall Time | $t_f$ | | | | 31 | | |
| **DRAIN−SOURCE DIODE CHARACTERISTICS** | | | | | | | |
| Forward Diode Voltage | $V_{SD}$ | $V_{GS}$ = 0 V, $I_S$ = 7.0 A | $T_J$ = 25°C | | 0.75 | 1.0 | V |
| | | | $T_J$ = 125°C | | 0.6 | | |
| Reverse Recovery Time | $t_{RR}$ | $V_{GS}$ = 0 V, $dI_S/dt$ = 100 A/μs, $I_S$ = 7.0 A | | | 28 | | ns |
| Charge Time | $t_a$ | | | | 14 | | |
| Discharge Time | $t_b$ | | | | 14 | | |
| Reverse Recovery Charge | $Q_{RR}$ | | | | 23 | | nC |

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

## TYPICAL PERFORMANCE CURVES

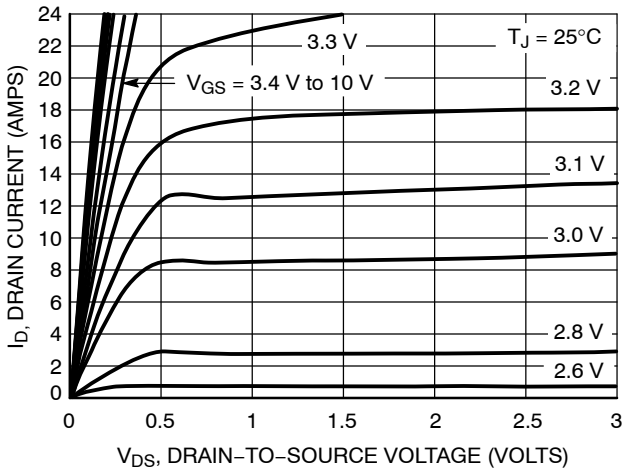


**Figure 1. On−Region Characteristics**

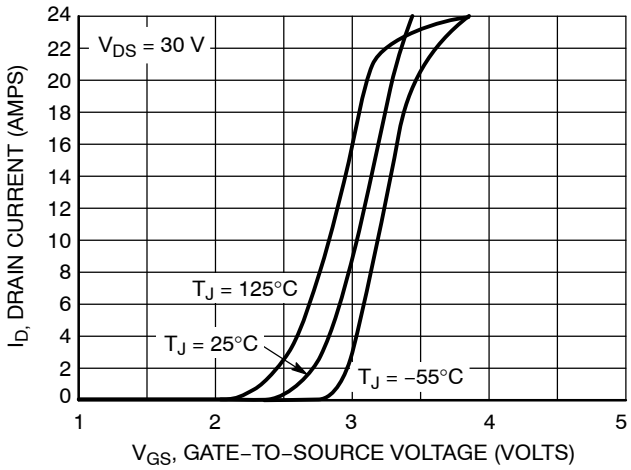


**Figure 2. Transfer Characteristics**

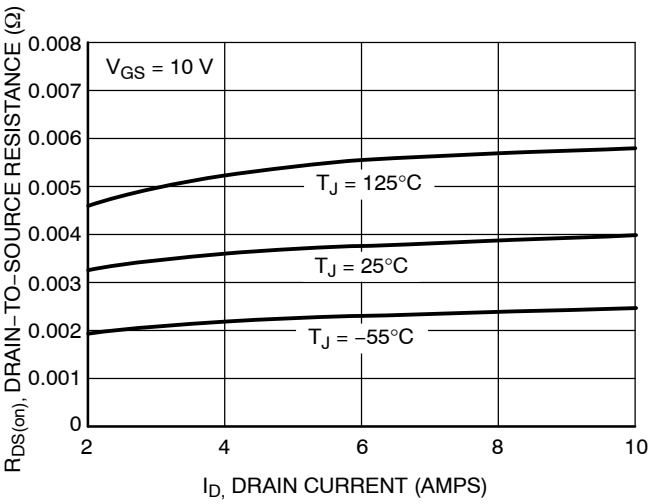


**Figure 3. On−Resistance vs. Drain Current**

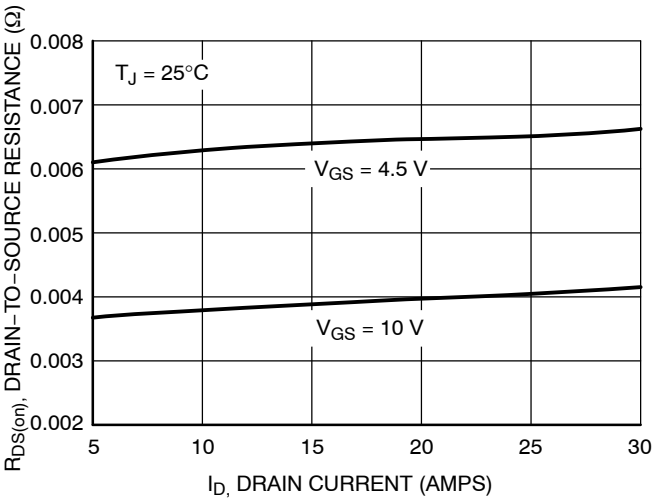


**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**

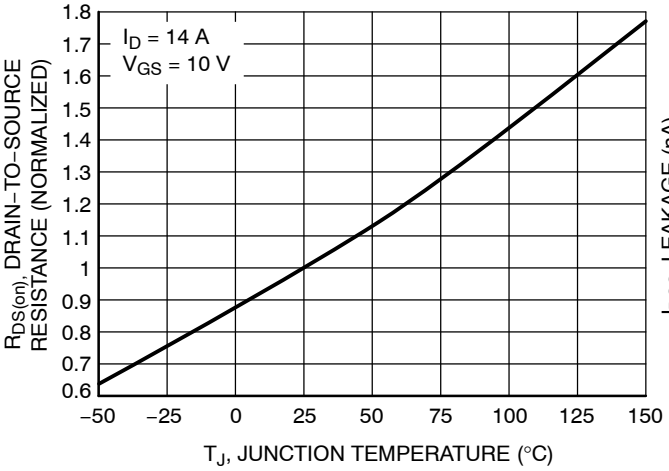


**Figure 5. On−Resistance Variation with Temperature**

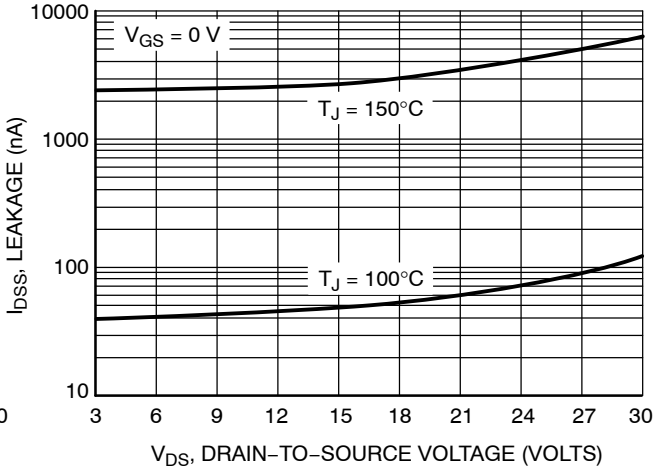


**Figure 6. Drain−to−Source Leakage Current vs. Voltage**

## TYPICAL PERFORMANCE CURVES

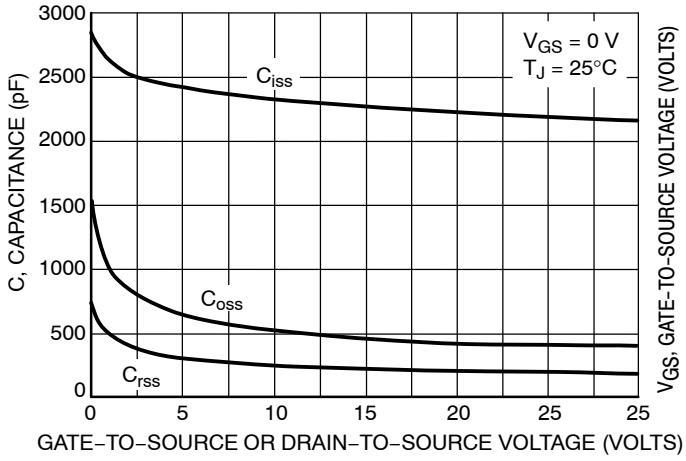


**Figure 7. Capacitance Variation**

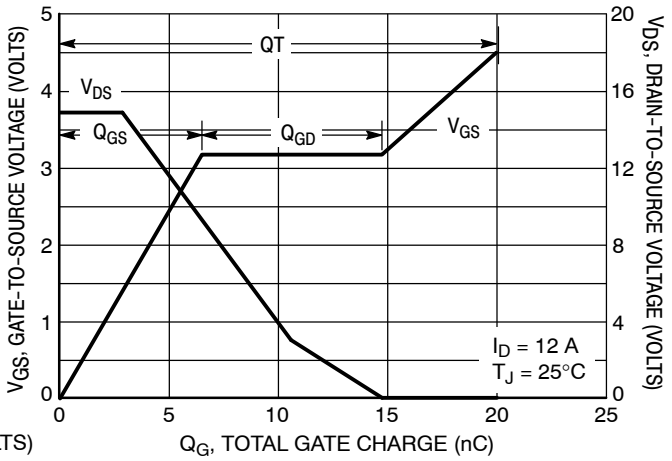


**Figure 8. Gate−To−Source and Drain−To−Source Voltage vs. Total Charge**

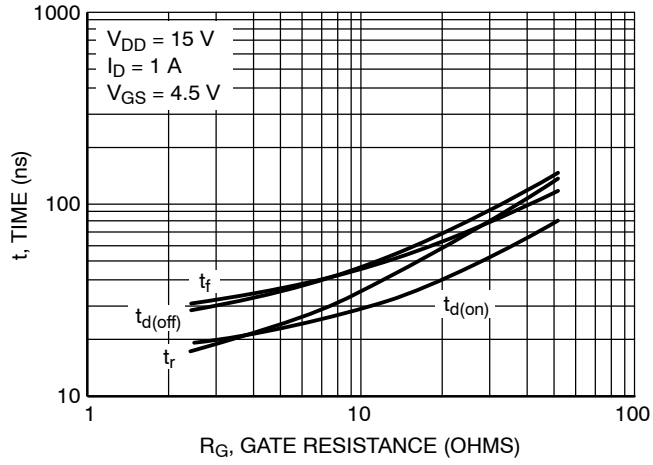


**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**

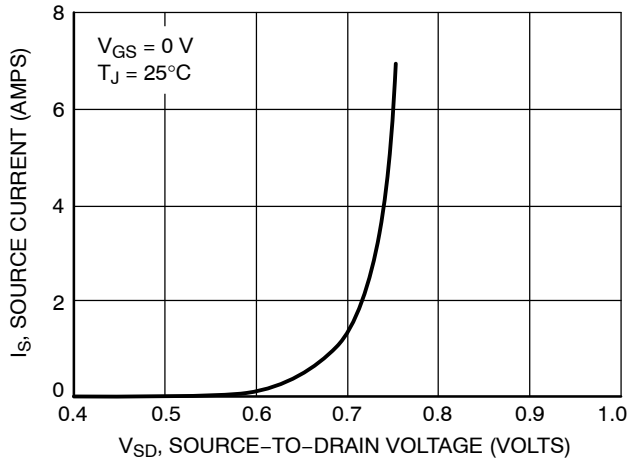


**Figure 10. Diode Forward Voltage vs. Current**

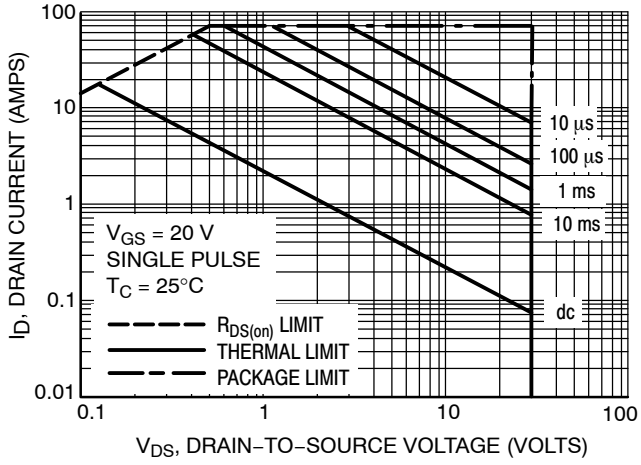


**Figure 11. Maximum Rated Forward Biased Safe Operating Area**

# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

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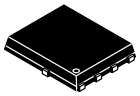
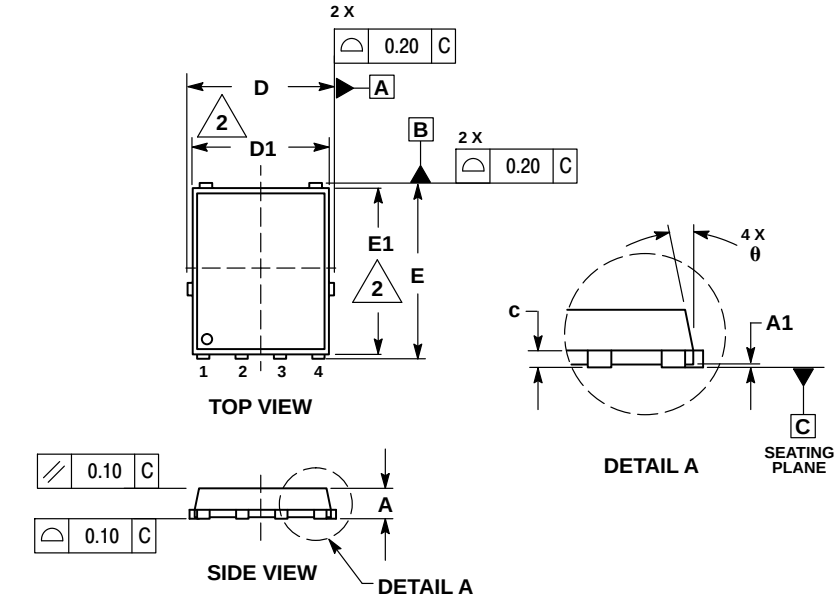


SCALE 2:1

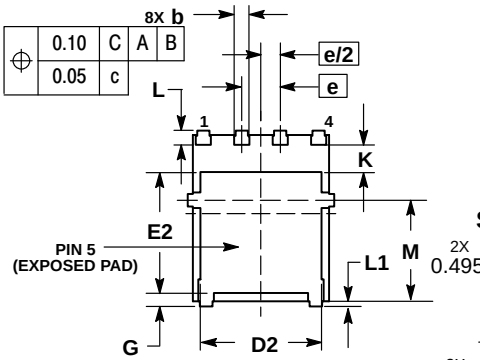
**DFN5 5x6, 1.27P**
**(SO−8FL)**
CASE 488AA
ISSUE N

DATE 25 JUN 2018

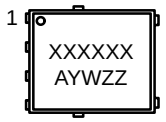



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | ––– | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| c | 0.23 | 0.28 | 0.33 |
| D | 5.00 | 5.15 | 5.30 |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.80 | 4.00 | 4.20 |
| E | 6.00 | 6.15 | 6.30 |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.45 | 3.65 | 3.85 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.575 | 0.71 |
| K | 1.20 | 1.35 | 1.50 |
| L | 0.51 | 0.575 | 0.71 |
| L1 | 0.125 REF | | |
| M | 3.00 | 3.40 | 3.80 |
| θ | 0 ° | ––– | 12 ° |



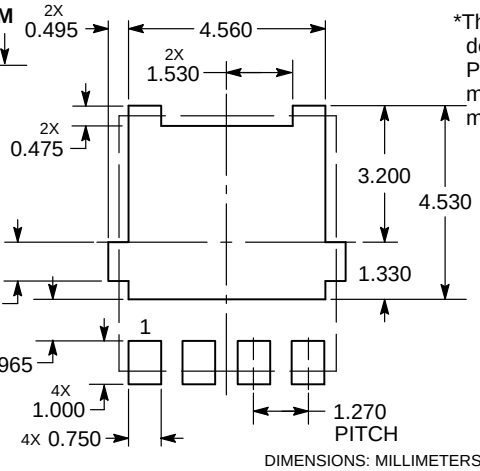

**GENERIC MARKING DIAGRAM***




XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

**RECOMMENDED SOLDERING FOOTPRINT***




DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | |
|---|---|---|
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| **DESCRIPTION:** | **DFN5 5x6, 1.27P (SO−8FL)** | **PAGE 1 OF 1** |


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